NSN 5962-01-370-0994

Memory Microcircuit - Page 1 of 2



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Maximum Power Dissipation Rating:

880.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

An/fps-124

Features Provided:

Schottky and bipolar

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Bipolar metal-oxide semiconductor

Case Outline Source And Designator:

D-8 mil-m-38510

Current Rating Per Characteristic:

-30.00 milliamperes collector cutoff current, dc, base open absolute and 5.00 milliamperes average forward current averaged over a full 60-hz cycle absolute

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, digital, schottky, bipolar 4096 prom

Voltage Rating And Type Per Characteristic:

-0.5 volts total supply and 7.0 volts total supply

Time Rating Per Chacteristic:

45.00 nanoseconds access

Memory Device Type:

Prom

Hybrid Technology Type:

Monolithic

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

20 printed circuit

Chalf I ifa

Specification Data:

67268-5962-8769002ra government standard and 56232-1219251-215 manufacturers source control

Departure From Cited Designator:

Altered by programming, marking & testing

NSN 5962-01-370-0994

Memory Microcircuit - Page 2 of 2

Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

A458a0

